



Preliminary Information DPI2100P45A5200

Press-Pack IGBT

DS6218-2 July 2018 (LN35909)

FEATURES

- Wide safe operating area
- 10µs short circuit withstand
- · Outstanding thermal cycling capability
- All-IGBT configuration
- High tolerance of non-uniform clamping pressure

APPLICATIONS

- High voltage DC transmission
- Flexible AC transmission systems
- High reliability inverters
- Motor controllers

ORDERING INFORMATION

Order As:

DPI2100P45A5200

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}		4500V
$V_{CE(sat)}$	(typ)	2.4V
I _C	(max)	2100A
I _{C(PK)}	(max)	4200A

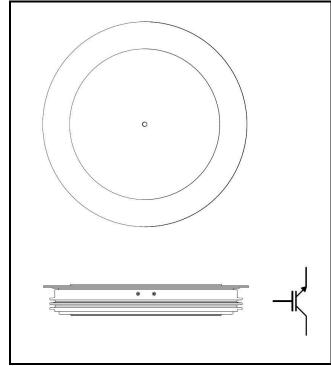


Fig.1 Circuit configuration



Fig. 2 Package



ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V$	4500	٧
V_{GES}	Gate-emitter voltage	-	±20	V
I _C	Continuous collector current	T _{case} = 95°C	2100	Α
I _{C(PK)}	Peak collector current	1ms, T _j = 125°C	4200	Α
P _{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}C, T_{j} = 125^{\circ}C$	22.7	kW

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
R _{th(j-c)} *	Thermal resistance – junction to case (collector side)	DC	-	0.0044	°C/W
R _{th(c-h)} *	Thermal resistance – case to heatsink (collector side)	Clamping force 70kN (with mounting compound)	-	0.0018	°C/W
T _{vj}	Virtual junction temperature	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	125	°C
Fm	Clamping force	-	65	75	kN

Note:

^{*} Heat transfer occurs primarily through the collector side of the device.



ELECTRICAL CHARACTERISTICS

 T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I _{CES}	Collector cut-off current	$V_{GE} = 0V$, $V_{CE} = V_{CES}$			5	mA
		$V_{GE} = 0V$, $V_{CE} = V_{CES}$, $T_{case} = 125$ °C		20	60	mA
I _{GES}	Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			10	μΑ
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 260$ mA, $V_{GE} = V_{CE}$		6.1		V
V _{CE(sat)}	Collector-emitter saturation voltage	$V_{GE} = 15V$, $I_C = 2100A$, $T_j = 25$ °C		2.4		V
		$V_{GE} = 15V$, $I_C = 2100A$, $T_j = 125$ °C		2.8		V
Qg	Gate charge	V _{GE} = ±15V		38		μC
SC _{Data}	Short circuit current, I _{SC}	$T_{j} = 125^{\circ}C$, $V_{CC} = 3400V$ $t_{p} \le 10\mu s$, $V_{GE} \le 15V$ $V_{CE (max)} = V_{CES} - L^{*} x dI/dt$ IEC 60747-9		10000		А

Note:

^{*} L is the circuit inductance



ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_{C} = 2100A$ $V_{GE} = \pm 15V$ $V_{CE} = 2800V$ $R_{G(ON)} = 1.5\Omega$		4700		ns
t _f	Fall time			1900		ns
E _{OFF}	Turn-off energy loss			9900		mJ
t _{d(on)}	Turn-on delay time	$R_{G(OFF)} = 4.7\Omega$ $C_{GE} = 330nF$		760		ns
t _r	Rise time	L _S ~ 220nH Freewheel diode type Dynex DPF2100P45A0052		420		ns
E _{ON}	Turn-on energy loss			6400		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_{C} = 2100A$ $V_{GE} = \pm 15V$ $V_{CE} = 2800V$ $R_{G(ON)} = 1.5\Omega$ $R_{G(OFF)} = 4.7\Omega$ $C_{GF} = 330nF$		4800		ns
t _f	Fall time			2900		ns
E _{OFF}	Turn-off energy loss			11000		mJ
t _{d(on)}	Turn-on delay time			720		ns
t _r	Rise time	L _S ~ 220nH Freewheel diode type		440		ns
E _{ON}	Turn-on energy loss	Dynex DPF2100P45A0052		8800		mJ



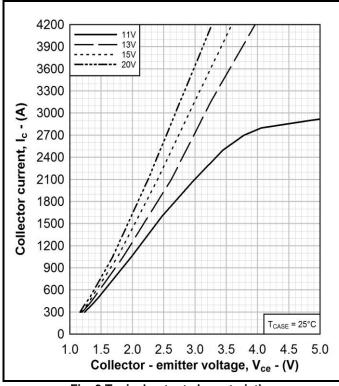


Fig. 3 Typical output characteristics

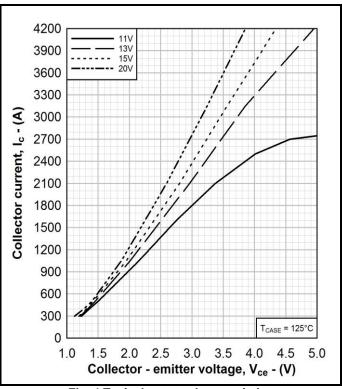


Fig. 4 Typical output characteristics

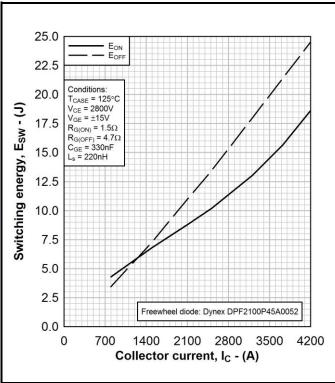


Fig. 5 Typical switching energy vs. collector current

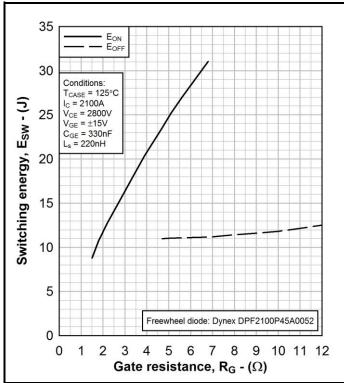
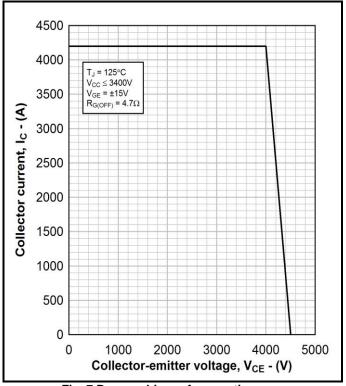


Fig. 6 Typical switching energy vs. gate resistance





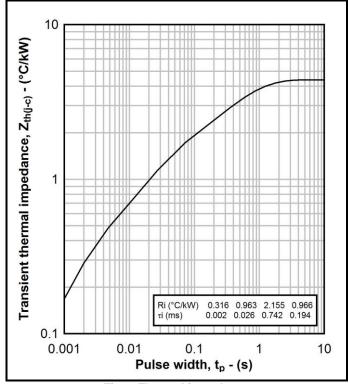


Fig. 7 Reverse bias safe operating area

Fig. 8 Thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.

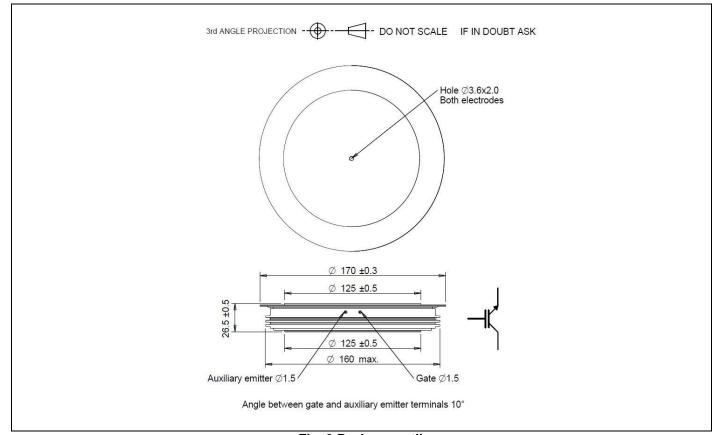


Fig. 9 Package outline



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The datasheet represents the product as it is now understood but details may change.

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